



**Dual Matched Instrumentation
Operational Amplifier**

FEATURES

- Extremely tight matching
- Offset match.....0.18mV Max..
- Channel separation..... 126 dB Min
- Low bias current.....2nA Max
- High R_{IN} 30M Ω Min ..
- Bias current match3nA Max
- Low noise0.6 μ V_{pp}Max

APPLICATIONS

- Sampling & Hold Amplifiers
- Integrators
- Medical Instrumentation
- Strain Gauge & Thermocouple
- Precision Absolute Value Circuits

PRODUCT DESCRIPTION

The ALPHA Semiconductor AS OP-10 is a dual-matched instrumentation operational amplifier that offers two independent monolithic high-performance operational amplifiers in a single 14-pin dual-in-line package. Tight matching between channels is provided on the main parameters including offset, tracking of offset vs. temperature, non-inverting bias current and common mode and power supply rejection ratios.

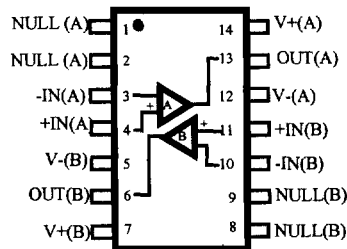
The OP-10 is available in several different grades. The AS OP-10 is available in hermetically sealed 14 pin dual-in-line package. The operating temperature is 0°C to 70°C and -55°C to +125°C.

ORDERING INFORMATION

Plastic DIP 14-PIN	TA=25°C V _{os} Max (mv)	Oper. Temp. Range
OP10EY	0.5	COM
OP10CY	0.5	COM

PIN CONNECTIONS

14-Pin EPOXY DIP



Top View

ABSOLUTE MAXIMUM RATINGS

Supply Voltage.....	±22V
Internal Power Dissipation (Note 1).....	500mW
Differential Input Voltage.....	±30V
Input Voltage (Note 2).....	±22V
Output Short-Circuit Duration.....	Indefinite
Storage Temperature Range	
Y Package.....	-65 to +150°C
Operating Temperature Range	
OP10A, OP10.....	-55 to +125°C
OP10E, OP10C.....	0 to +70°C
Dice Junction Temperature(T _J).....	-65 to +150°C
Lead Temperature (Soldering, 60 Sec.).....	300°C

NOTES:

1. See Table for maximum ambient temperature rating and derating factor.
2. Absolute maximum ratings apply to both DICE and packaged parts unless otherwise noted.
3. For Supply voltages less than ±22V, the absolute maximum input voltage is equal to the supply voltage.

PACKAGE TYPE	MAXIMUM AMBIENT TEMPERATURE FOR RATING	DERATE ABOVE MAXIMUM AMBIENT TEMPERATURE
14-Pin Plastic DIP	106°C	11.3 mW/°C

ELECTRICAL CHARACTERISTICS at V_S=±15V, T_a=25°C, unless otherwise specified.

Parameter	Symbol	Conditions	OP-10			Units
			Min.	Typ.	Max.	
Input Offset Voltage	V _{OS}			0.2	0.5	mV
Long-Term Input Offset Voltage Stability	V _{OS} /Time	(Note 1)		0.25	1.0	μV/M ₀
Input Offset Current	I _{OS}			1.0	2.8	nA
Input Bias Current	I _B			±1	±3	nA
Input Noise Voltage (Note 2)	e _{npp}	0.1Hz to 10Hz		0.35	0.6	μV _{p-p}
Input Noise Voltage Density (Note 2)	e _n	f _o =10Hz		10.3	18.0	nV/√Hz
Input Noise Voltage Density (Note 2)	e _n	f _o =100Hz		10.0	13.0	nV/√Hz
Input Noise Voltage Density (Note 2)	e _n	f _o =1000Hz		9.6		nV/√Hz
Input Noise Current (Note 2)	i _{npp}	0.1 Hz to 10Hz		14	30	pA _{p-p}
Input Noise Current Density (Note 2)	i _n	f _o =10Hz		0.32	0.80	pA/√Hz
Input Noise Current Density (Note 2)	i _n	f _o =100 Hz		0.14	0.23	pA/√Hz
Input Noise Current Density (Note 2)	i _n	f _o =1000Hz		0.12	0.17	pA/√Hz
Input Resistance-Differential-Mode	R _{in}	(Note 3)	20	60		MΩ
Input Resistance-Common Mode	R _{inCM}			200		GΩ
Input Voltage Range	IVR		±13	±14		V
Common-Mode Rejection Ratio	CMRR	V _{CM} =±13.0	110	126		dB
Power Supply Rejection Ratio	PSRR	V _S =±3V to ±18		4	10	μV/V
Large-Signal Voltage Gain	A _{VO}	R _L ≥ 2kΩ, V _o = ±10V	200	500		V/mV
Large-Signal Voltage Gain	A _{VO}	R _L ≥ 2kΩ, V _o = ±0.5V V _S = ±3V (Note 3)	200	150	500	V/mV
Output Voltage Swing	V _o	R _L ≥ 10kΩ	±12.5	±13.0		V
Output Voltage Swing	V _o	R _L ≥ 2kΩ	±12.0	±12.8		V
Output Voltage Swing	V _o	R _L ≥ 1kΩ	±10.5	±12.0		V
Slewing Rate	SR	R _L ≥ 2kΩ		0.17		V/μs
Closed-Loop Bandwidth	BW	A _{vcl} = ±1.0 (Note 1)		0.6		MHz
Open-Loop Output Resistance	R _o	V _o = 0, I _o = 0		60		Ω
Power Consumption	P _d	Each Amplifier		90	120	mW
Power Consumption	P _d	V _S = ±3V, No load		4	6	mW
Offset Adjustment Range		R _p = 20kΩ		±4		mV
Input Capacitance	C _{in}			8		pF

Notes:

1. Long term input offset voltage stability refers to the averaged trend line of V_{os}
 2. Sample tested
 3. Guaranteed by design.
- V_s . Time over extended periods after the first 30 days of operation. Excluding the initial hour of operation, changes in V_{os} during the first 30 operating days is typically 2.5 mV.

INDIVIDUAL AMPLIFIER CHARACTERISTICS at $V_s = \pm 15V$, $T_a = 25^\circ C$, unless otherwise specified.

Parameter	Symbol	Conditions	OP-10E			OP-10C			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Input Offset Voltage	V_{os}		0.2	0.5		0.2	0.5	mV	
Long-Term Input Offset Voltage Stability	V_{OS}/Time	(Note 1)	0.3	1.5		0.5		$\mu V/M_O$	
Input Offset Current	I_{os}		1.2	3.8		1.8	6.0	nA	
Input Bias Current	I_B		± 1.2	± 4.0		± 1.8	± 7.0	nA	
Input Noise Voltage (Note 2)	e_{npp}	0.1Hz to 10Hz	0.35	0.6		0.38	0.65	μV_{p-p}	
Input Noise Voltage Density (Note 2)	e_n	$f_o = 10\text{Hz}$	10.3	18.0		10.3	20.0	nV/ $\sqrt{\text{Hz}}$	
Input Noise Voltage Density (Note 2)	e_n	$f_o = 100\text{Hz}$	10.0	13.0		10.2	13.5	nV/ $\sqrt{\text{Hz}}$	
Input Noise Voltage Density (Note 2)	e_n	$f_o = 1000\text{Hz}$	9.6	11.0		9.8	11.5	nV/ $\sqrt{\text{Hz}}$	
Input Noise Current (Note 2)	i_{npp}	0.1 Hz to 10Hz	14	30		15	35	pA_{p-p}	
Input Noise Current Density (Note 2)	i_n	$f_o = 10\text{Hz}$	0.32	0.80		0.35	0.90	$\text{pA}/\sqrt{\text{Hz}}$	
Input Noise Current Density (Note 2)	i_n	$f_o = 100\text{Hz}$	0.14	0.23		0.15	0.27	$\text{pA}/\sqrt{\text{Hz}}$	
Input Noise Current Density (Note 2)	i_n	$f_o = 1000\text{Hz}$	0.12	0.17		0.13	0.18	$\text{pA}/\sqrt{\text{Hz}}$	
Input Resistance-Differential-Mode	R_{in}	(Note 3)	15	50		8	33	M Ω	
Input Resistance-Common Mode	R_{inCM}			160			120	G Ω	
Input Voltage Range	IVR		± 13	± 14		± 13	± 14	V	
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm 13.0$	106	123		100	120	dB	
Power Supply Rejection Ratio	PSRR	$V_S = \pm 3V$ to ± 18	4	20		10	32	$\mu V/V$	
Large-Signal Voltage Gain	A_{VO}	$R_L \geq 2k\Omega$, $V_o = \pm 10V$	200	500		120	400	V/mV	
Large-Signal Voltage Gain	A_{VO}	$R_L \geq 2k\Omega$, $V_o = \pm 0.5V$, $V_S = \pm 3V$ (Note 3)	150	500		100	400	V/mV	
Output Voltage Swing	V_o	$R_L \geq 10k\Omega$	± 12.5	± 13.0		± 12.0	± 13.0	V	
Output Voltage Swing	V_o	$R_L \geq 2k\Omega$	± 12.0	± 12.8		± 11.5	± 12.8	V	
Output Voltage Swing	V_o	$R_L \geq 1k\Omega$	± 10.5	± 12.0		± 12.0		V	
Slewing Rate	SR	$R_L \geq 2k\Omega$		0.17			0.17	V/ μs	
Closed-Loop Bandwidth	BW	$A_{vcl} = +1.0$ (Note 1)		0.6			0.6	MHz	
Open-Loop Output Resistance	R_o	$V_o = 0$, $I_o = 0$		60			60	Ω	
Power Consumption	P_d	Each Amplifier	90	120		95	150	mW	
Power Consumption	P_d	$V_S = \pm 3V$, No load	4	6		4	8	mW	
Offset Adjustment Range		$R_p = 20k\Omega$		± 4			± 4	mV	
Input Capacitance	Cin			8			8	pF	

ELECTRICAL AMPLIFIER CHARACTERISTICS at $V_S = \pm 15V$, $-55^\circ C \leq T_a \leq +125^\circ C$, unless otherwise specified.

Parameter	Symbol	Conditions	OP-10			Units
			Min.	Typ.	Max.	
Input Offset Voltage	V_{os}			0.3	0.7	mV
Average Input Offset Voltage Drift Without External Trim	TCV_{os}	(Note 1)		0.7	2.0	$\mu V/^\circ C$
With External Trim	TCV_{os}	$R_p = 20\Omega$ (note 3)		0.3	1.0	$\mu V/^\circ C$
Input Offset Current	I_{os}			1.8	5.6	nA
Average Input Offset Current Drift	TCI_{os}	Note 2		8	50	$\mu A/^\circ C$
Input Bias Current	I_B			± 2	± 6	nA
Average Input Bias Current Drift	TCI_B	Note 2		13	50	$\mu A/^\circ C$
Input Voltage Range	IVR		± 13.0	± 13.5		V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm 13.0V$	106	123		dB
Power Supply Rejection Ratio	PSRR	$V_S = 3V$ to $\pm 18V$		5	20	$\mu V/V$
Large-Signal Voltage Gain	A_{vo}	$R_L \geq 2\Omega$, $V_o = \pm 10V$	150	400		V/mV
Output Voltage Swing	V_o	$R_L \geq 2\Omega$	± 12	± 12.6		V

MATCHING CHARACTERISTICS at $V_S = \pm 15V$, $T_a = +25^\circ C$, Unless otherwise specified.

Parameter	Symbol	Conditions	OP-10			Units
			Min.	Typ.	Max.	
Input Offset Voltage	V_{os}			0.12	0.5	mV
Average Noninverting Bias Current	I_{B^+}			± 1.3	± 4.5	nA
Noninverting Offset Current	I_{OS^+}			1.1	4.5	nA
Inverting Offset Current	I_{OS^-}			1.1	4.5	nA
Common-Mode Rejection Ratio Match	CMRR	$V_{CM} = \pm 13V$	106	120		dB
Power Supply Rejection Ratio Match	PSRR	$V_S = 3V$ to ± 18		4	20	$\mu V/V$
Channel Separation	CS	(Note 2)	126	140		dB

MATCHING CHARACTERISTICS at $V_S = \pm 15V$, $-55^\circ C \leq T_a \leq +125^\circ C$, unless otherwise noted.

Parameter	Symbol	Conditions	OP-10			Units
			Min.	Typ.	Max.	
Input Offset Voltage Match	V_{os}			0.2	0.9	mV
Input Offset Voltage Tracking Drift Without External Trim	TCV_{os}	(Note 2)		0.9	2.5	$\mu V/^\circ C$
With External Trim	TCV_{os}	$R_p = 20\Omega$ (note 3), Channel A only		0.4	1.2	$\mu V/^\circ C$
Average Noninverting Bias Current	I_{B^+}			± 2.4	± 8.0	nA
Average Drift of Noninverting Bias Current	TCI_{B^+}	Note 2		15		$\mu A/^\circ C$
Noninverting Offset Current	I_{OS^+}			2.4	90	nA
Average Drift of Noninverting Offset Current	TCI_{OS}	Note 2		18		$\mu A/^\circ C$
Inverting Offset Current	I_{OS^-}			2.4	90	nA
Common-Mode Rejection Ratio Match	CMRR	$V_{CM} = \pm 13V$	103	117		dB
Power Supply Rejection Ratio Match	PSRR	$V_S = \pm 3V$ to ± 18		7	32	$\mu V/V$

Notes:

1. Long term input offset voltage stability refers to the averaged trend line of V_{os} Vs. Time over extended periods after the first 30 days of operation. Excluding the initial hour of operation, changes in V_{os} during the first 30 operating days is typically 2.5 mV.
2. Sample tested
3. Guaranteed by design.

INDIVIDUAL CHARACTERISTICS at $V_s = \pm 15V$, $0^\circ C \leq T_a \leq 70^\circ C$, unless otherwise specified.

Parameter	Symbol	Conditions	OP-10E			OP-10C			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Input Offset Voltage	V_{os}			0.25	0.6		0.35	1.6	mV
Average Input Offset Voltage Drift Without External Trim	TCV_{os}	(Note 1)		0.7	2.0		1.2	4.5	$\mu V/^\circ C$
With External Trim	TCV_{os}	$R_p = 20\Omega$ (note 3)		0.3	1.0		0.4	1.5	$\mu V/^\circ C$
Input Offset Current	I_{os}			1.4	5.3		2.0	8.0	nA
Average Input Offset Current Drift	TCI_{os}	Note 2		8	50		12	50	$\mu A/^\circ C$
Input Bias Current	I_B			± 1.5	± 5.5		± 2.2	± 9.0	nA
Average Input Bias Current Drift	TCI_B	Note 2		13	50		18	50	$\mu A/^\circ C$
Input Voltage Range	IVR		± 13.0	± 13.5		± 13.0	± 13.5		V
Common-Mode Rejection Ratio	CMRR	$V_{CM} \pm 13.0 V$	103	123		97	120		dB
Power Supply Rejection Ratio	PSRR	$V_s = \pm 3V$ to $\pm 18V$		7	32		10	51	$\mu V/V$
Large-Signal Voltage Gain	A_{vo}	$R_{Lz} = 2\Omega$, $V_o = \pm 10V$	100	400		100	400		V/mV
Output Voltage Swing	V_o	$R_1 \geq 2\Omega$	± 12.0	± 12.6		± 11.0	± 12.6		V

Notes:

1. Long term input offset voltage stability refers to the averaged trend line of V_{os} vs. Time over extended periods after the first 30 days of operation. Excluding the initial hour of operation, changes in V_{os} during the first 30 operating days are typically 2.5 mV.
2. Sample tested
3. Guaranteed by design.

MATCHING CHARACTERISTICS at $V_s = \pm 15V$, $T_a = +25^\circ C$, Unless otherwise specified.

Parameter	Symbol	Conditions	OP-10E			OP-10C			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Input Offset Voltage Match	V_{os}			0.12	0.5		0.3		mV
Average Noninverting Bias Current	I_{B+}			± 1.3	± 4.5		± 2.0		nA
Noninverting Offset Current	I_{OS+}			1.1	4.5		1.8		nA
Inverting Offset Current	I_{OS-}			1.1	4.5		1.8		nA
Common-Mode Rejection Ratio Match	CMRR	$V_{CM} = \pm 13V$	106	120		117			dB
Power Supply Rejection Ratio Match	PSRR	$V_s = 3V$ to ± 18		4	20		5		$\mu V/V$
Channel Separation	CS	(Note 1)	126	140		126	137		dB

MATCHING CHARACTERISTICS at $V_s = \pm 15V$, $0^\circ C \leq T_a \leq 70^\circ C$, unless otherwise specified.

Parameter	Symbol	Conditions	OP-10E			OP-10C			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Input Offset Voltage Match	V_{os}			0.18	0.7		0.4		mV
Input Offset Voltage Tracking Drift Without External Trim	TCV_{os}	(Note 1)		0.9	2.3		1.3		$\mu V/^\circ C$
With External Trim	TCV_{os}	$R_p = 20\Omega$ (note 3), Channel A only		0.3	0.9		0.6		$\mu V/^\circ C$
Average Noninverting Bias Current	I_{B+}			± 2.0	± 6.0		± 2.8		nA
Average Drift of Noninverting Bias Current	TCI_{B+}	Note 1		12	40		18		$\mu A/^\circ C$
Noninverting Offset Current	I_{OS+}			2.0	6.0		2.8		nA
Average Drift of Noninverting Offset Current	TCI_{OS+}	Note 1		15	50		20		$\mu A/^\circ C$
Input Offset Current	I_{OS-}			2.0	6.0		2.8		nA
Common-Mode Rejection Ratio Match	CMRR	$V_{CM} = \pm 13V$	103	117		114			dB
Power Supply Rejection Ratio Match	PSRR	$V_s = \pm 3V$ to ± 18		6	32		8		$\mu V/V$

Notes:

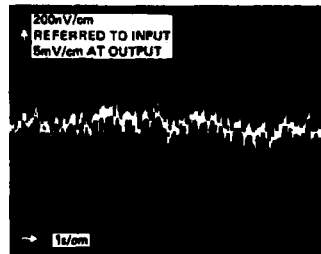
1. Sample tested
2. Guaranteed by design.

OFFSET NULLING CIRCUIT

BURN-IN CIRCUIT

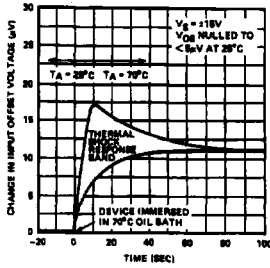
TYPICAL PERFORMANCE

OP-10 LOW FREQUENCY NOISE

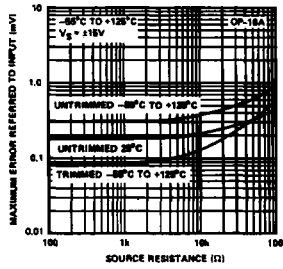


TYPICAL PERFORMANCE

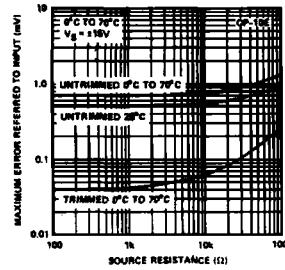
OFFSET VOLTAGE CHANGE DUE TO THERMAL SHOCK



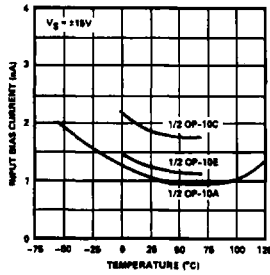
MATCHING CHARACTERISTIC MAXIMUM INPUT ERROR vs SOURCE RESISTANCE



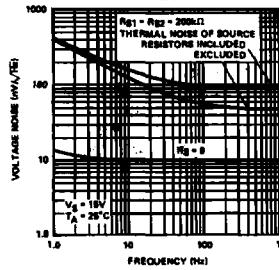
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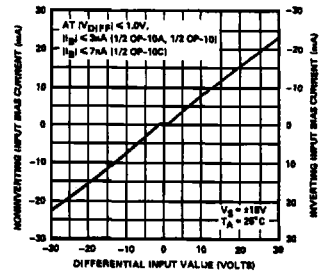
INPUT BIAS CURRENT vs TEMPERATURE



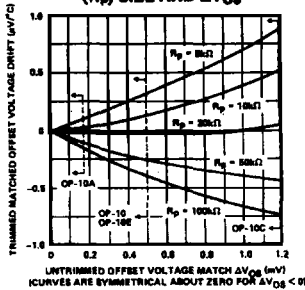
VOLTAGE NOISE DENSITY vs FREQUENCY



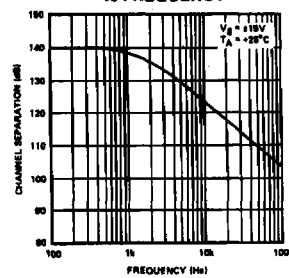
INPUT BIAS CURRENT vs DIFFERENTIAL INPUT VOLTAGE



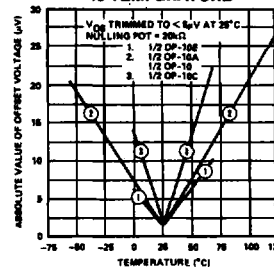
MATCHING CHARACTERISTICS TRIMMED MATCHED OFFSET VOLTAGE DRIFT AS A FUNCTION OF TRIMMING POT (R_p) SIZE AND ΔV_{OS}



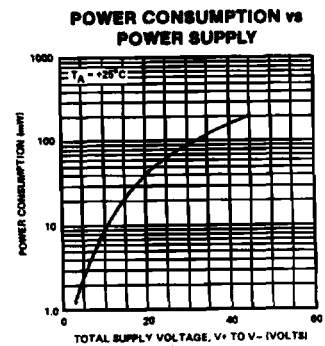
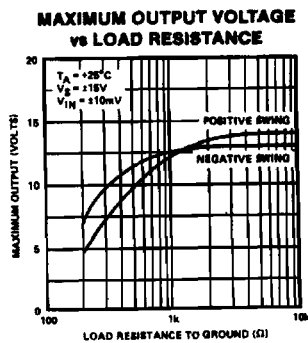
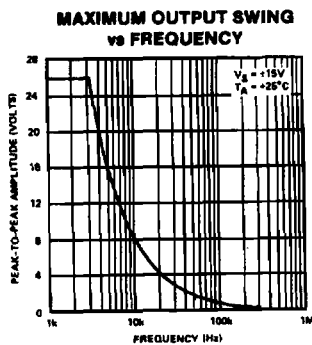
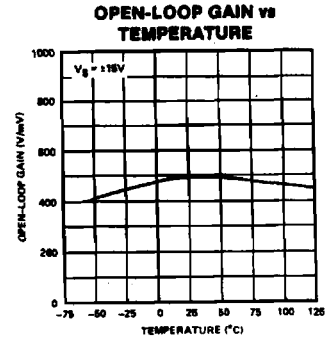
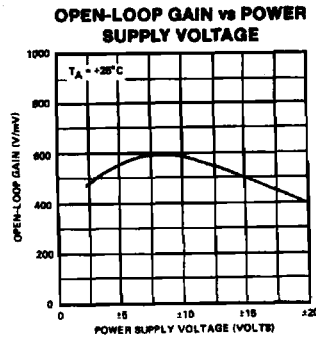
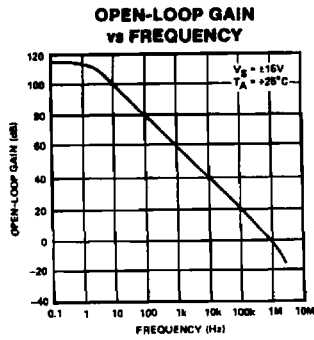
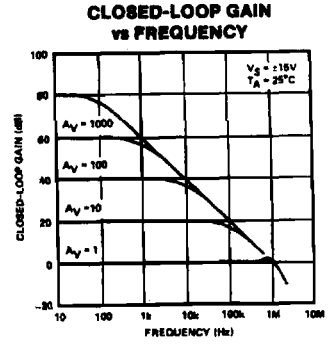
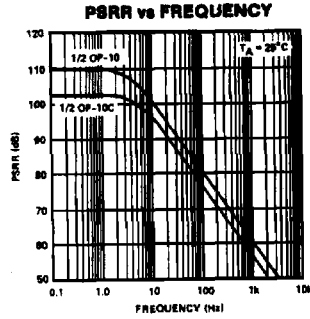
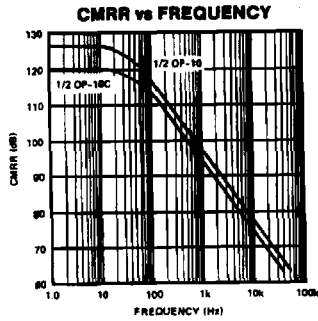
MATCHING CHARACTERISTICS CHANNEL SEPARATION vs FREQUENCY



TRIMMED OFFSET VOLTAGE vs TEMPERATURE



TYPICAL PERFORMANCE



APPLICATION INFORMATION

DUAL MATCHED OP-AMP ADVANTAGES

Dual matched operational amplifiers provide a powerful tool in solving some difficult circuit design problems. Circuits include true instrumentation amplifiers, high common-mode rejection DC amplifiers, extremely low drift, low DC drift active filters, dual tracking voltage references and many other demanding applications. These designs all require good matching between two operational amplifiers.

The circuit below shows the how the errors can be reduced through these advantages. If the resistors are matched, then the gain of each side will be identical. If the offset voltage of each amplifier is matched, then the net differential voltage at the amplifiers output will be zero. The impedance of each input, both common-mode and differential-mode, are extremely high, an important feature not possible with single operational amplifier circuits.

POWER SUPPLIES

The positive supply terminals are completely independent and may be powered by separate supplies if desired. However, this method would sacrifice the advantages of power supply rejection ratio matching. The negative supply terminals are both connected to the common substrate and must be tied to the same voltage.

OFFSET TRIMMING

Each amplifier has its own offset voltage trimming. The performance over temperature is done by trimming one side to match the offset of the other side.

The AS OP-10 provides the lowest drift when trimmed with 20k Ω potentiometer. This value provides about $\pm 4\text{mV}$ of adjustment range.